TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

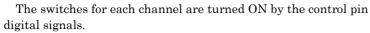
# TC7MZ4051FK,TC7MZ4052FK,TC7MZ4053FK

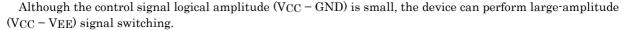
TC7MZ4051FK 8-Channel Analog Multiplexer/Demultiplexer TC7MZ4052FK Dual 4-Channel Analog Multiplexer/Demultiplexer

TC7MZ4053FK Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC7MZ4051/4052/4053FK are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

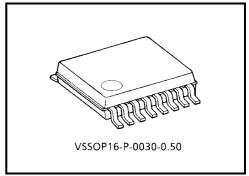
The TC7MZ4051/4052/4053FK offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel  $\times$  2 configuration, and the 4053 has a 2-channel  $\times$  3 configuration.





For example, if  $V_{CC} = 3 \text{ V}$ , GND = 0 V, and  $V_{EE} = -3 \text{ V}$ , signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the VCC). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC7MZ4051/4052/4053FK can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.



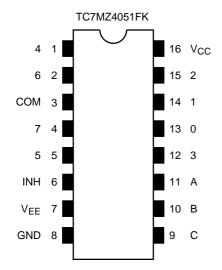
Weight: 0.02 g (typ.)

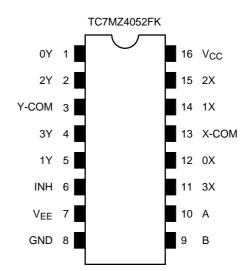
#### **Features**

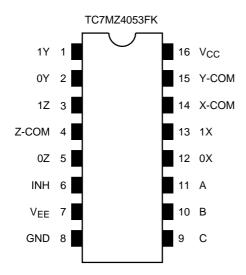
- Low ON resistance:  $R_{on} = 22 \Omega$  (typ.) (V<sub>CC</sub> V<sub>EE</sub> = 3 V)  $R_{on} = 15 \Omega$  (typ.) (V<sub>CC</sub> - V<sub>EE</sub> = 6 V)
  - High speed:  $t_{pd} = 3$  ns (typ.) (V<sub>CC</sub> = 3.0 V)
- Low power dissipation:  $ICC = 4 \mu A \text{ (max)}$  (Ta = 25°C)
- Input level:  $V_{IL} = 0.8 \text{ V (max)} (V_{CC} = 3 \text{ V})$ 
  - $V_{IH} = 2.0 \text{ V (min)} (V_{CC} = 3 \text{ V})$
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053



### Pin Assignment (top view)







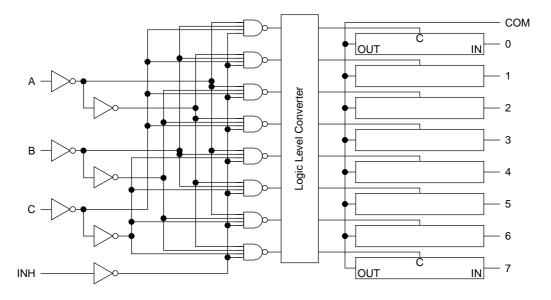
#### **Truth Table**

	Contro	I Inputs		"ON" Channel				
Inhibit	C*	В	Α	MZ4051FK	MZ4052FK	MZ4053FK		
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	_	0X, 0Y, 1Z		
L	Н	L	Н	5	_	1X, 0Y, 1Z		
L	Н	Н	L	6	_	0X, 1Y, 1Z		
L	Н	Н	Н	7	_	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

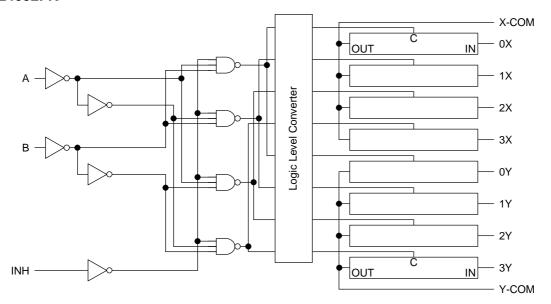
X: Don't care, \*: Except MZ4052FK

## **System Diagram**

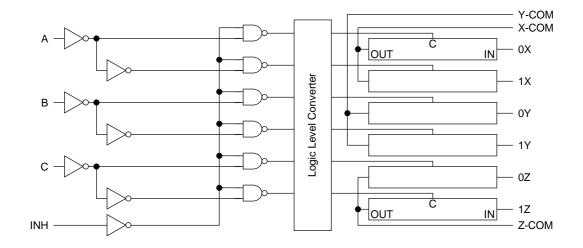
### **TC7MZ4051FK**



#### **TC7MZ4052FK**



#### **TC7MZ4053FK**



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# **Absolute Maximum Ratings**

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~7.0	V	
Fower Supply Voltage	V <sub>CC</sub> ~V <sub>EE</sub>	-0.5~7.0	V	
Control input voltage	V <sub>IN</sub>	-0.5~7.0	V	
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> - 0.5~V <sub>CC</sub> + 0.5	V	
Input diode current	I <sub>IK</sub>	-20	mA	
I/O diode current	I <sub>IOK</sub>	±20	mA	
Switch through current	I <sub>T</sub>	±25	mA	
DC V <sub>CC</sub> or ground current	Icc	±50	mA	
Power dissipation	PD	180	mW	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
	V <sub>CC</sub>	2~6		
Power supply voltage	V <sub>EE</sub>	-4~0	V	
	V <sub>CC</sub> ~V <sub>EE</sub>	2~6		
Input voltage	V <sub>IN</sub>	0~6.0	V	
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> ~V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V	
Imput rise and fall time	ui/uv	0~20 (V <sub>CC</sub> = 5 ± 0.5 V)	115/V	



### **Electrical Characteristics**

### **DC Electrical Characteristics**

Characteristics		Symbol	ol Test Condition				Га = 25°(	C	Ta = -4	0~85°C	Unit
Character	Onarasionolios		rest Condition	V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
					2.0	1.5	_	_	1.5	_	
	High-level	V <sub>IH</sub>			3.0	2.0	_	_	2.0	_	
	i ligit-level	VIΗ	_		4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2	_	_	4.2	_	V
Input voltage					2.0		_	0.5	_	0.5	V
	Low-level	V <sub>IL</sub>			3.0		_	0.8	_	0.8	
	LOW-level	V IL	_		4.5	_	_	1.35	_	1.35	
					6.0	_	_	1.8	_	1.8	
			\\ \\ or\\	GND	2.0	_	200	_	_	_	
			$V_{IN} = V_{IL}$ or $V_{IH}$ $V_{I/O} = V_{CC}$ to $V_{EE}$ $I_{I/O} = 2$ mA	GND	3.0	_	45	86	_	108	Ω
				GND	4.5		24	37	_	46	
ON resistance		R <sub>ON</sub>		-3.0	3.0		17	26	_	33	
ON Tesistance		TON	$V_{IN} = V_{IL}$ or $V_{IH}$ $V_{I/O} = V_{CC}$ or $V_{EE}$ $I_{I/O} = 2$ mA	GND	2.0	_	28	73	_	84	
				GND	3.0		22	38	_	44	
				GND	4.5		17	27	_	31	
			11/0 – 2 111/4	-3.0	3.0		15	24	_	28	
			V V 22V	GND	2.0		10	25	_	35	Ω
Difference of Ol resistance betw		ΔR <sub>ON</sub>	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$	GND	3.0		5	15	_	20	
switches	een	ANON	$I_{I/O} = 2 \text{ mA}$	GND	4.5		5	13	_	18	
			1 /O = 2 111A	-3.0	3.0		5	10	_	15	
Input/Output lea	akage		$V_{OS} = V_{CC}$ or GND	GND	3.0		_	±0.25		±2.5	
current (switch OFF)		l <sub>OFF</sub>	$V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0	_	_	±0.5	_	±5.0	μА
Input/Output leakage current (switch ON, output open)		I <sub>IN</sub>	$V_{OS} = V_{CC}$ or GND	GND	3.0	_	_	±0.25	_	±2.5	μА
			V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub>	-3.0	3.0	_	_	±0.5	_	±5.0	
Control input current		I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND	GND	6.0	_	_	±0.1	_	±0.1	μΑ
Quiocoont cum	ly ourront			GND	3.0	_	_	4.0	_	40.0	^
Quiescent supp	ny current	Icc	$V_{IN} = V_{CC}$ or GND	-3.0	3.0		_	8.0	_	80.0	μΑ

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## AC Electrical Characteristics ( $C_L = 50 \text{ pF}$ , Input: $t_r = t_f = 3 \text{ ns}$ , GND = 0 V)

Characteristics	Symbol	Test Condition					Ta = 25°C			Ta = -40~85°C	
Characteristics	Symbol			V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
				GND	2.0	_	3.2	6.0	_	6.9	
Phase difference between	φΙ/О	All type	ae	GND	3.0		1.8	3.0	_	3.5	ns
input and output	ψι/Ο	All type	,,,	GND	4.5		1.3	1.8	_	2.1	113
				-3.0	3.0		1.1	1.3	_	1.5	
				GND	2.0		9.0	17	_	20	
Output enable time	t <sub>pZL</sub>	Figure	1 (Note 1)	GND	3.0	_	5.7	9.0	_	11	ns
Output enable time	t <sub>pZH</sub>	rigure	1 (14016-1)	GND	4.5		4.5	6.0	_	7.0	113
				-3.0	3.0	_	5.8	8.0	_	10	
				GND	2.0	_	13.5	21	_	25	- ns
Output disable time	t <sub>pLZ</sub>	Figure	1 (Note 1)	GND	3.0		11.3	15	_	18	
Output disable time	t <sub>pHZ</sub>	riguie i (Ne	1 (14016-1)	GND	4.5		10.3	12	_	14	
				-3.0	3.0		10.9	13	_	15	
Control input capacitance	C <sub>in</sub>	All type	es (Note 2)	_			5	10	_	10	pF
		4051	Figure 2 (Note 2)				11	25		25	
COMMON terminal capacitance	C <sub>IS</sub>	4052		-3.0	3.0	_	9	20	_	20	pF
·		4053					7	15		15	
		4051	Figure 2				6	13		13	
SWITCH terminal capacitance	Cos	4052	(Note 2)	-3.0	3.0	—	6 1	13	_	13	pF
'		4053	(Note 2)				6	13		13	
		4051					3	6		6	
Feedthrough capacitance	C <sub>IOS</sub>	4052	Figure 2 (Note 2)	-3.0	3.0	0 —	3	3 6 -	—	6	pF
		4053					3	6		6	
		4051					14				
Power dissipation capacitance	C <sub>PD</sub>	4052	Figure 2 (Note 3)	GND	6.0	_	24	-   -	_		pF
		4053	, ,				18				

Note1:  $R_L = 1 k\Omega$ 

Note2:  $C_{in}$ ,  $C_{IS}$ ,  $C_{OS}$  and  $C_{IOS}$  are guaranteed by the design.

Note3: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance of IC which is calculated from the

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operating current consumption without load.

Average operating current can be obtained by the equation:

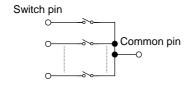
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 



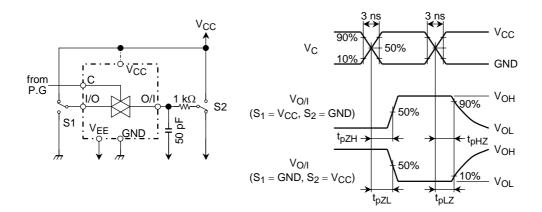
# \*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

Characteristics	Symbol	Test Condition			Тур.	Unit	
Characteristics	Symbol	rest Condition		V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	тур.	Offic
			$V_{IN} = 2.0 V_{p-p}$	0	3.0	0.100	
Sine Wave Distortion (T.H.D)	Adjust $f_{IN}$ voltage to obtain at $V_{OS}$ .  Increase $f_{IN}$ frequency untimeter reads $-3dB$ . $R_L = 50~\Omega, C_L = 10~pF, f_{IN} = 1~MHz, sine wave$ Figure 3 $V_{IN} \text{ is centered at } (V_{CC} - V_{CC})$ Adjust input for 0dBm. $R_L = 600~\Omega, C_L = 50~pF, f_{IN}$ Figure 4 $R_L = 50~\Omega, C_L = 10~pF, f_{IN}$	$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF},$ $f_{INI} = 1 \text{ kHz}$	V <sub>IN</sub> = 4.0 V <sub>p-p</sub>	0	4.5	0.030	%
			$V_{IN} = 6.0 V_{p-p}$	-0.3	3.0	0.020	
			4051			150	
			4052	0	3.0	180	
		Adjust f <sub>IN</sub> voltage to obtain 0dBm at Vos	4053			200	MHz
Fraguency reenenee		Increase f <sub>IN</sub> frequency until dB	4051			150	
Frequency response (switch ON)	f <sub>max</sub>		4052	0	4.5	180	
(SWILCH ON)			4053			200	
			4051		3.0	150	
		gu. o o	4052	-3.0		180	
			4053			200	
		V <sub>IN</sub> is centered at (V <sub>CC</sub> – V <sub>EE</sub> )/2.	0	3.0	-45	dB	
		Adjust input for 0dBm.		0	4.5		-45
		$R_L = 600 \Omega$ , $C_L = 50 pF$ , $f_{IN} = 1 M$		4.5	-45		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	-45		
			0	3.0	-60		
		$R_L = 50 \Omega$ , $C_L = 10 pF$ , $f_{IN} = 1 MH$	0	4.5	-60		
			-3.0	3.0	-60		
Crosstalk		$R_L = 600 \Omega$ , $C_L = 50 pF$ , $f_{IN} = 1 M$	Hz, square wave	0	3.0	90	
(control input to signal		$(t_f = t_f = 6 \text{ ns})$	0	4.5	150	mV	
output)		Figure 5		-3.0	3.0	120	
Crosstalk		Adjust V <sub>IN</sub> to obtain 0dBm at input	0	3.0	-45		
(between any switches)		$R_L = 600 \Omega$ , $C_L = 50 pF$ , $f_{IN} = 1 M$	0	4.5	-45	dB	
(between any switches)		Figure 6		-3.0	3.0	-45	

<sup>\*:</sup> These characteristics are determined by design of devices.



#### **AC Test Circuit**



 $\label{eq:figure 1} \textbf{Figure 1} \quad t_{\text{pLZ}},\, t_{\text{pHZ}},\, t_{\text{pZL}},\, t_{\text{pZH}}$ 

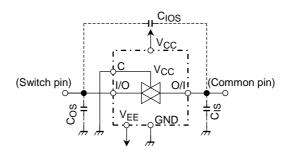


Figure 2 C<sub>IOS</sub>, C<sub>IS</sub>, C<sub>OS</sub>

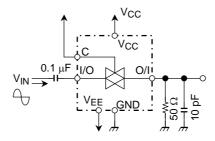


Figure 3 Frequency Response (switch on)

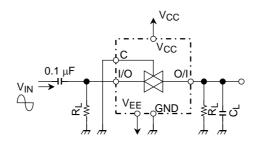


Figure 4 Feedthrough

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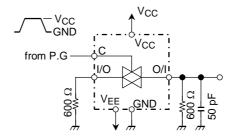


Figure 5 Cross Talk (control input to output signal)

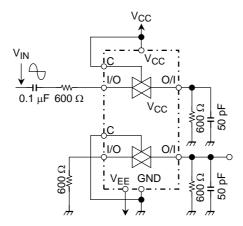
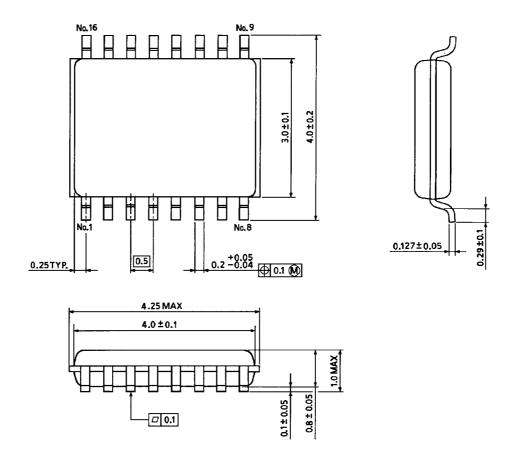


Figure 6 Cross Talk (between any two switches)

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## **Package Dimensions**



Weight: 0.02 g (typ.)

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